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TITLE: Method for manufacturing semiconductor device

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BASIC-ABSTRACT:

NOVELTY - A fabrication method of a semiconductor device is provided to prevent an erosion of metal interconnections by dry-cleaning using a gas of fluoride(F) series after etching a metal film.

DETAILED DESCRIPTION - An oxide layer(11) is deposited on a semiconductor substrate(10). A metal film, such as aluminum or aluminum alloy is deposited on the oxide layer(11). After forming a photoresist pattern on the resultant structure, a metal pattern(120) is formed by selectively etching the exposed metal film using chlorinated mixed gases. Cl2 gas and BCl3 gas are used as the Chlorinated mixed gases. Then, the resultant structure is dry-cleaned by using a gas of fluoride(F) series. Preferably, CHF3 gas is used as the gas of fluoride(F) series. At this time, argon(Ar) gas is mixed to the gas of fluoride(F) series.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD MANUFACTURE SEMICONDUCTOR DEVICE

DERWENT-CLASS: L03 U11

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